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INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet A1 of

Complete if Known

Application Number	10/772,882
Filing Date	February 5, 2004
First Named Inventor	Saxler
Group Art Unit	2811
Examiner Name	Jerome Jackson, Jr.
Attorney Docket Number	5308-389

## U.S. PATENTS AND PATENT PUBLICATIONS

Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
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Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T
		Office	Number	Kind Code (if known)			
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	17.	PCT	WO 01/57929 A1		Cree Lighting Company	08-09-2001	
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	19.	EP	0 563 847 A2		Matsushita Electric Industrial Co., Ltd.	10-06-1993	

## OTHER NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
	20.	Breitschadel et al., "Minimization of Leakage Current of Recessed Gate AlGaIn/GaN HEMTs by Optimizing the Dry-Etching Process," <i>Journal of Electronic Materials</i> , Vol. 28, No. 12 (1999).	
	21.	Burn et al., "Recessed Gate GaN MODFETS," <i>Solid State Electronics</i> , Vol. 41, No. 2, pp. 247-50 (1997)	
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	25.	Heikman, Sten J., <i>MOCVD Growth Technologies for Applications in AlGaIn/GaN High Electron Mobility Transistors</i> , Dissertation, University of California—Santa Barbara, 190 pages (2002).	
	26.	Karmalkar et al., "Enhancement of Breakdown Voltage in AlGaIn/GaN High Electron Mobility Transistors Using a Field Plate," <i>IEEE Transactions on Electron Devices</i> , Vol. 48, No. 8 (2001).	
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	30.	Sriram et al., "RF Performance of AlGaIn/GaN MODFET's on High Resistivity SiC Substrates," <i>Presentation at Materials Research Society Fall Symposium</i> , 1997.	
	31.	Sriram et al., "SiC and GaN Wide Bandgap Microwave Power Transistors," <i>IEEE Samoff Symposium</i> , March 18, 1998.	

Examiner Signature

Date Considered

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.